

isc Silicon NPN Power Transistor

3DA752

DESCRIPTION

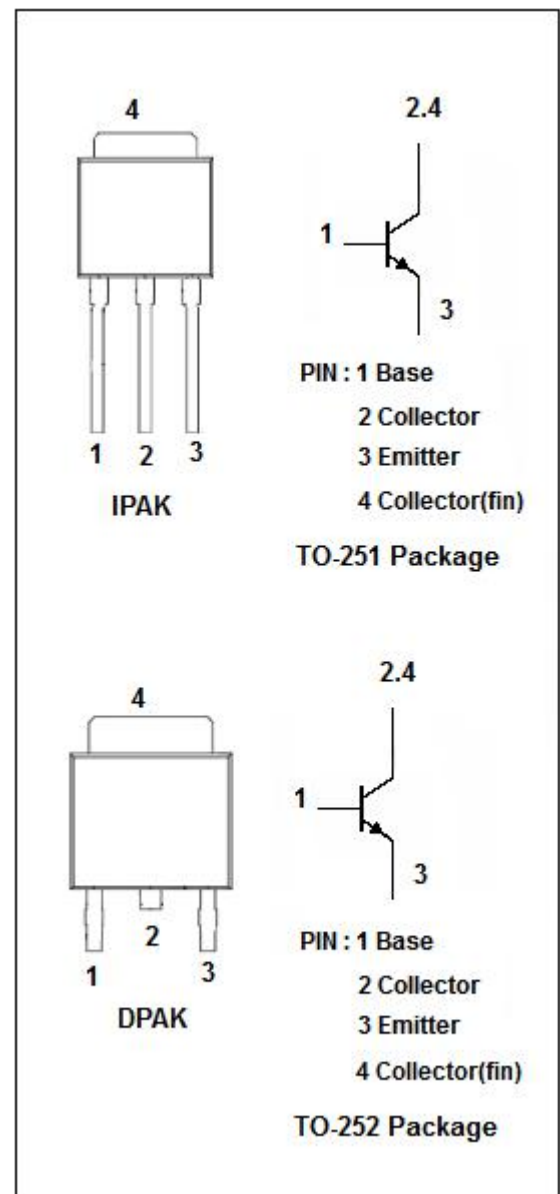
- Low $V_{CE(sat)}$
- Small and slim package
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Power dissipation

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	30	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	2	A
P_C	Collector Power Dissipation	1.2	W
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}\text{C}$



isc Silicon NPN Power Transistor**3DA752****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE(sat)} -1	Collector-Emitter Saturation Voltage	I _C = 2A; I _B = 200mA			0.8	V
V _{CE(sat)} -2	Collector-Emitter Saturation Voltage	I _C = 1.5A; I _B = 30mA			2.0	V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = 100uA; I _B = 0	40			V
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 10mA; I _B = 0	30			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 1mA; I _C = 0	5			V
I _{CBO}	Collector Cutoff Current	V _{CB} = 40V; I _E = 0			0.1	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0			0.1	μ A
h _{FE}	DC Current Gain	I _C = 0.5A; V _{CE} = 2V	100		400	
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = 10V; f= 1.0MHz		13		pF
f _T	Current-Gain—Bandwidth Product	I _C = 500mA; V _{CE} = 5V		120		MHz

◆ h_{FE} Classifications

O	Y	G
100-200	160-320	200-400

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Outline Drawing

